

IN THE CLAIMS:

Please cancel claims 28-38, 40-46, and 49 without prejudice and amend the claims as follows:

1-38. (Cancelled)

39. (Currently Amended) The substrate of claim 37 A substrate, comprising:
a first dielectric layer comprising silicon, carbon, and nitrogen;
a nitrogen free silicon carbide cap adjacent the first dielectric layer; and
a second dielectric layer comprising silicon, oxygen, and carbon adjacent the
nitrogen free silicon carbide cap; and

one or more etch dielectric layers adjacent the second dielectric layer, wherein
the one or more etch dielectric layers comprise:

a nitrogen doped silicon carbide layer adjacent the second dielectric layer;
and

nitrogen free silicon carbide cap adjacent the nitrogen doped silicon
carbide layer.

40-46. (Cancelled)

47. (Currently Amended) The substrate of claim 44 A substrate, comprising:
a first dielectric layer comprising silicon, carbon, and nitrogen;
a nitrogen-free silicon and carbon containing material adjacent the first dielectric
layer;

a second dielectric layer comprising silicon, oxygen, and carbon on the nitrogen-
free silicon and carbon containing material; and

an etch stop layer adjacent the second dielectric layer, wherein the etch stop
layer comprises a nitrogen doped silicon carbide layer.

48. (Currently Amended) The substrate of claim 44 A substrate, comprising:
a first dielectric layer comprising silicon, carbon, and nitrogen;

a nitrogen-free silicon and carbon containing material adjacent the first dielectric layer;

a second dielectric layer comprising silicon, oxygen, and carbon on the nitrogen-free silicon and carbon containing material; and

an etch stop layer adjacent the second dielectric layer, wherein the etch stop layer comprises:

 a nitrogen doped silicon carbide layer adjacent the second dielectric layer;
 and

a nitrogen free silicon carbide cap adjacent the nitrogen doped silicon carbide layer.

49. (Cancelled)